



# LC6006

## LDO mode OVP with Integrated P-MOSFET

### DESCRIPTION

The LC6006 is Li+ charger IC with integrated P-MOSFET. The device is fabricated with advanced CMOS technology to achieve maintaining low static power dissipation over a very broad VCC operating range.

The LC6006 integrates a P-MOSFET and Schottky diode which is normally a discrete device employed for conventional battery charging design of mobile phone system. In addition to that, LC6006 works like a LDO mode to keep CHRIN voltage stable when ACIN goes high. And thus it will not trigger the CHRIN pin over-voltage protection when ACIN voltage increased to as high as 15V.

The LC6006 provides complete Li+ charger protections and saves the external MOSFET and Schottky diode for the charger of cell phone's PMIC. It is available in a DFN2x2-8L package.

The above features and small package make the LC6006 an ideal part for cell phones applications.

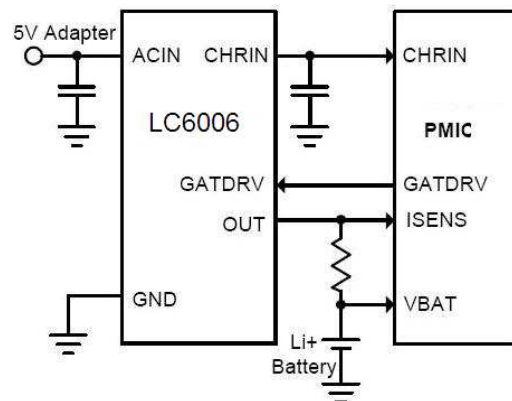
### FEATURES

- A Built-In P-MOSFET
- LDO mode makes CHRIN voltage stable around 5.5V
- Range of operation input voltage: Max 15V
- Charging current up to 1A
- Environment Temperature: -20°C~85°C

### APPLICATIONS

- Cell phone and other portable device

### APPLICATION CIRCUIT



### ORDERING INFORMATION / PIN CONFIGURATION / MARKING

LC6006CKBTR DFN2x2-8L	LC6006CB6TR SOT23-6L	Top Marking
		<p>OB<u>YW</u></p>

YW means the year and week parts being manufactured, subjected to change. OB is the code of the product; it will not be changed on any part.

## ABSOLUTE MAXIMUM RATING <sup>(Note1)</sup>

Parameter	Symbol	Rate	Unit
ACIN Input Voltage (ACIN to GND)	$V_{ACIN}$	-0.3~15	V
CHRIN to GND Voltage	$V_{CHRIN}$	-0.3~6	V
GATDRV to GND Voltage	$V_{GATDRV}$	-0.3~ $V_{CHRIN}$	V
OUT to GND Voltage	$V_{OUT}$	-0.3~6	V
Output power limit, $I_{out} \times (V_{ACIN}-V_{OUT})$	$P_D$	0.75	W
Maximum Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-40 to 150	
Maximum Lead Soldering Temperature, 10 Seconds	$T_{SDR}$	260	

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired. Exposure to absolute maximum rating conditions for extended periods may destroy the device.

## THERMAL RESISTANCE RATING

Parameter	Device	Symbol	Typical	Unit
Junction-to-Ambient Resistance in Free Air <sup>(Note2)</sup>	DFN2x2-8	$\theta_{JA}$	80	°C /W
	SOT23-6	$\theta_{JA}$	235	°C /W

Note 2:  $\theta_{JA}$  is measured with the component mounted on a high effective thermal conductivity test board in free air. The exposed pad of DFN2x2-8 is soldered directly on the PCB.

## THERMAL CONSIDERATION

Even though LC6006 can handle charge current larger than 1A, it is also limited by the power dissipation of the package DFN2x2-8L. The DFN2x2 package has a thermal pad exposed, and it should be tightly soldered to bottom PCB with a large coil area to dissipate the heat. In general, to have the LC6006 to work under a safe condition, one should take DFN2x2 power limit as 0.75W, and if the dropout voltage is 1.5V, one is suggested to set the charging current to be less than 500mA.

## RECOMMENDED OPERATION CONDITIONS

Symbol	Parameter	Range	Unit
$V_{ACIN}$	ACIN Input Voltage (ACIN to GND)	4.5~10	V
$I_{out}$	Output Current	0~700	mA
$T_A$	Ambient Temperature	-40~85	°C
$T_J$	Junction Temperature	-40~125	°C

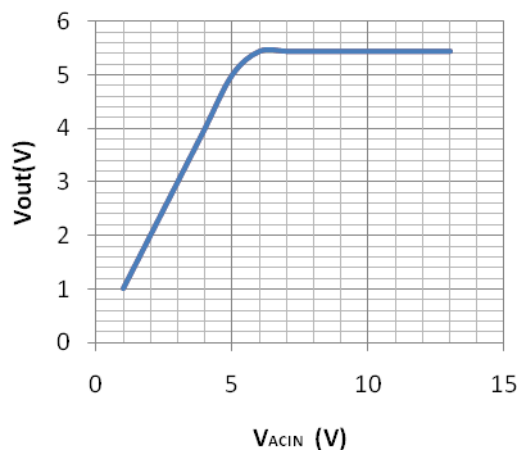
## ELECTRICAL CHARACTERISTICS

$T_J=25^\circ\text{C}$

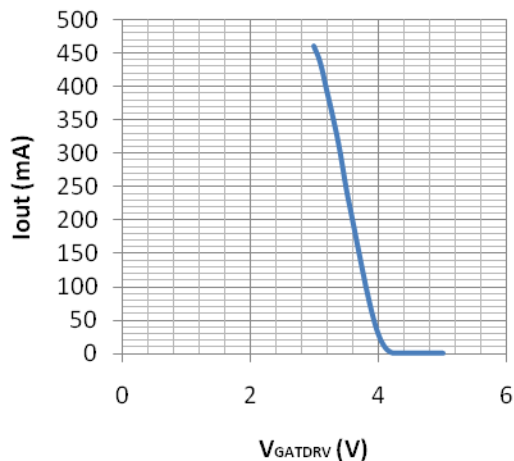
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{th}$	Threshold Voltage	$I_{ds}=-1\mu\text{A}$ , $V_{ds}=V_{gs}$	-1.0	-0.7	-0.4	V
$V_{CHRIN2}$	CHRIN Voltage	$V_{IN}=6.0\text{V}$ , $I_{CHRIN}=50\text{mA}$	5.0	5.5	6.0	V
$I_{Dss1}$	off-state leakage	$V_{OUT}=0$ , $V_{IN}=10\text{V}$ , $V_{GATDRV}=V_{CHRIN1}$	-	-	1	$\mu\text{A}$
$I_{Dss2}$	reverse block leakage	$V_{OUT}=5\text{V}$ , $V_{IN}=0$ , $V_{GATDRV}=V_{CHRIN1}=0\text{V}$	-	2	5	$\mu\text{A}$
$I_{dson}$	On-state drain current	$V_{IN}=5\text{V}$ , $V_{OUT}=4\text{V}$ , $V_{GATDRV}=1\text{V}$	0.9	1.2	1.5	A
$R_{dson}$	$V_{ds}/I_{dson}$	$V_s=5\text{V}$ , $V_g=1\text{V}$ , $V_d=4\text{V}$	0.5	0.75	1	ohm

## TYPICAL PERFORMANCE CHARACTERISTICS $T=25^{\circ}\text{C}$ unless specified.

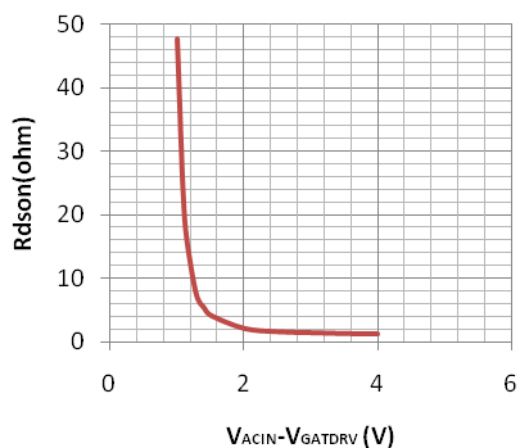
### Line Regulation



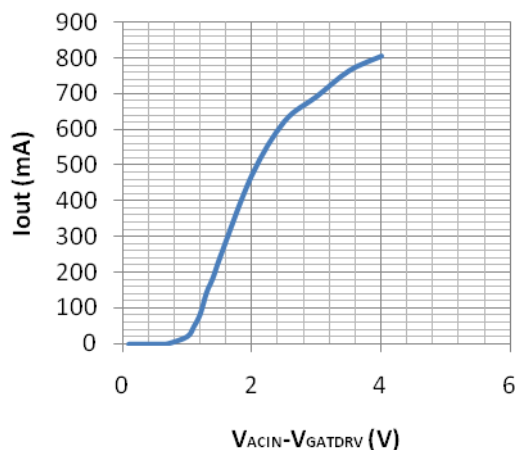
### Charger Current Vs $V_{\text{GATDRV}}$



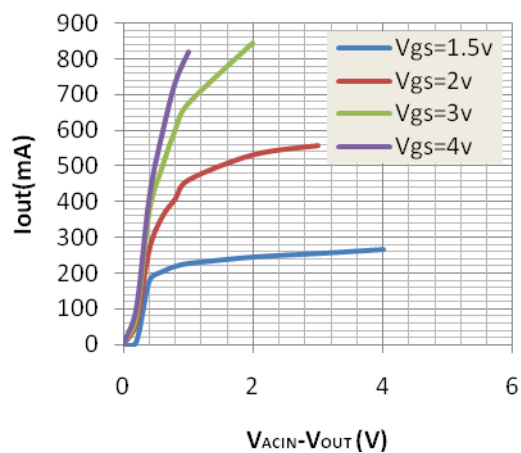
### On Resistance



### Transfer Character



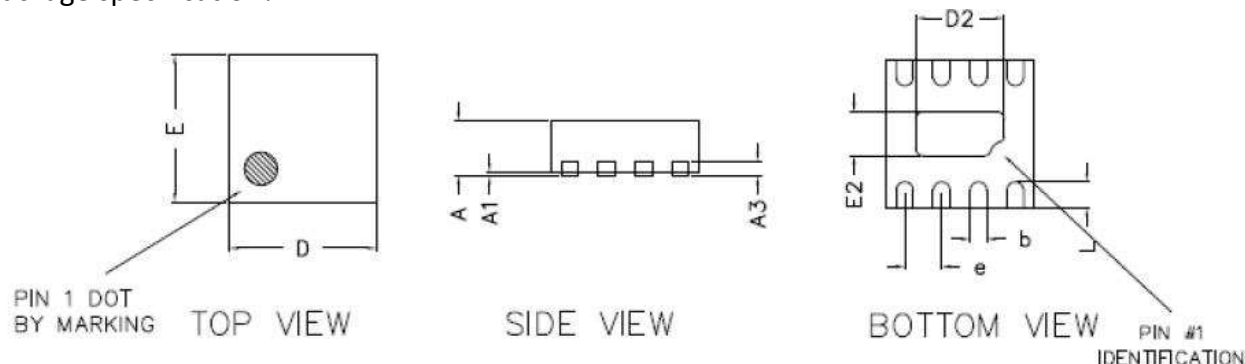
### Output Character



## PACKAGE OUTLINE

Package	DFN2x2-8	Devices per reel	3000	Unit	mm
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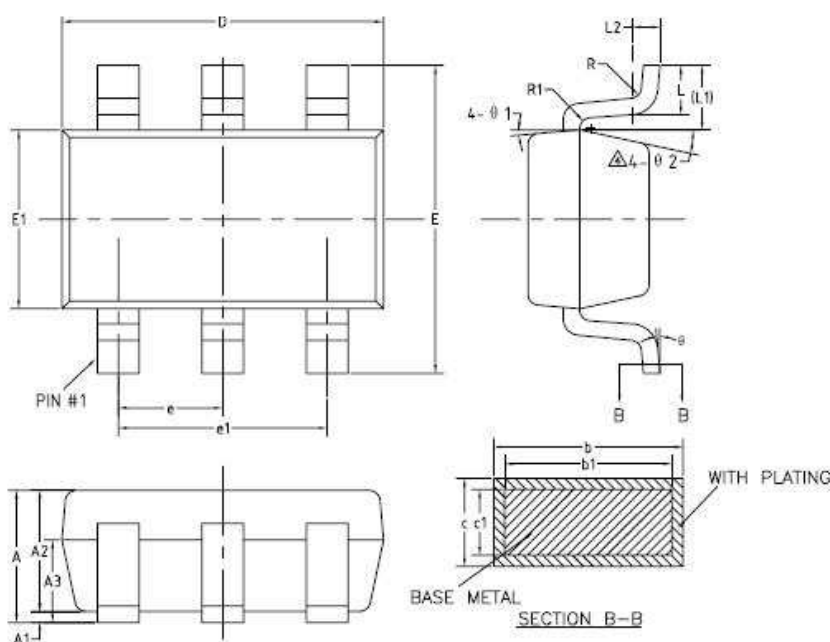
Package specification:



COMMON DIMENSIONS(MM)			
PKG. REF.	W: VERY VERY THIN		
	MIN.	NOM.	MAX
A	0.70	0.75	0.80
A1	0.00	—	0.05
A3	0.2 REF.		
D	1.95	2.00	2.05
E	1.95	2.00	2.05
b	0.18	0.23	0.30
L	0.25	0.35	0.45
D2	1.05	1.20	1.30
E2	0.45	0.60	0.70
e	0.50 BSC		

Package	SOT23-6	Devices per reel	3000	Unit	mm
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Package specification:



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	—	—	1.25
A1	0	—	0.15
A2	1.00	1.10	1.20
A3	0.60	0.65	0.70
b	0.36	—	0.50
b1	0.36	0.38	0.45
c	0.14	—	0.20
c1	0.14	0.15	0.16
D	2.826	2.926	3.026
E	2.60	2.80	3.00
E1	1.526	1.626	1.726
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.35	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
R	0.10	—	—
R1	0.10	—	0.20
θ	0°	—	8°
θ 1	3°	5°	7°
θ 2	6°	—	14°

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